

ABSTRACT OF THE DISCLOSURE

A protective insulating film is deposited over first and second field-effect transistors formed on a semiconductor substrate. A capacitor composed of a capacitor lower electrode, a capacitor insulating film composed of an insulating metal oxide film, and a capacitor upper electrode is formed on the protective insulating film. A first contact plug formed in the protective insulating film provides a direct connection between the capacitor lower electrode and an impurity diffusion layer of the first field-effect transistor. A second contact plug formed in the protective insulating film provides a direct connection between the capacitor upper electrode and an impurity diffusion layer of the second field-effect transistor.